

MGF7124A

1.9GHz BAND AMPLIFIER MMIC

DESCRIPTION

MGF7124A is a monolithic microwave integrated circuit for use in 1.9GHz band power amplifiers.

FEATURES

- High output power
 $P_{O}=26\text{dBm}, \pi/4\text{DQPSK}$
- Small size
 $5.8 \times 12.2 \times 1.8\text{mm}$
- Light weight
- Surface mount package
- Low supply voltage operation
 $V_{D}=4.8\text{V}$
- Enable to control gain
 $V_{G\text{dual}}=0/-4\text{V}$

APPLICATION

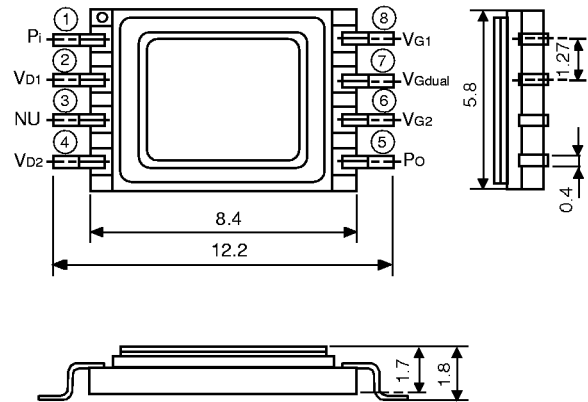
Base-station of Japanese personal handyphone system(PHS)

QUALITY GRADE

- IG

OUTLINE DRAWING

Unit: millimeters



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|----------|------------------|--------------------|-----------------|
| P_i | : RF INPUT | V_{G1} | : 1st GATE BIAS |
| V_{D1} | : 1st DRAIN BIAS | V_{G2} | : 2nd GATE BIAS |
| V_{D2} | : 2nd DRAIN BIAS | $V_{G\text{dual}}$ | : GAIN CONTROL |
| GND | : GND | P_o | : RF OUTPUT |

GC-3

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Ratings	Unit
V_{D1}, V_{D2}	Drain voltage	5.5	V
$V_{G1}, V_{G2}, V_{G\text{dual}}$	Gate voltage	-5.5	V
I_{D1}, I_{D2}, I_{D3}	Drain current	500	mA
P_i	Input power	10	dBm
$T_{C(\text{op})}$	Operating case temperature	-20 to +90	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-35 to +120	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

Symbol	Parameter	Test conditions (Note1)	Limits			Unit
			Min	Typ	Max	
f	Frequency		1.89	-	1.92	GHz
V_D	Drain supply voltage		4.8	5.0	5.2	V
G_P	Power gain	$P_O=26\text{dBm}, f=1.9\text{GHz}, \pi/4\text{DQPSK}$	21	-	-	dB
I_{Dt}	Total drain current		-	300	-	mA
G_{con}	Gain control range	$V_{G\text{dual}}=0/-4\text{V}, P_O=26\text{dBm}, f=1.9\text{GHz}$	20	-	-	dB
A.C.P ($\pm 600\text{kHz}$)	Adjacent channel power	$P_O=26\text{dBm}, f(\text{ACP})=\pm 600\text{kHz}, f=1.9\text{GHz}, \pi/4\text{DQPSK}$	-	-	-56	dBc
A.C.P ($\pm 900\text{kHz}$)		$P_O=26\text{dBm}, f(\text{ACP})=\pm 900\text{kHz}, f=1.9\text{GHz}, \pi/4\text{DQPSK}$	-	-	-62	dBc

Note1: $Z_S=Z_L=50\Omega, I_{D1}\text{-bias}=I_{D1}+I_{D2}=280\text{mA}$